

A7 33. (Amended) ~~1B~~ The integrated circuit of claim 32 wherein the control stack of each MOS transistor comprises a gate stack including an oxide layer, polysilicon layer, silicide layer, another oxide layer, and a nitride layer.

A8 35. (Amended) ~~1B~~ The integrated circuit of claim 34 wherein the electromagnetic radiation comprises collimated light.

37. (New) ~~1B~~ The integrated circuit of claim 30 wherein an insulating spacer layer is disposed between the control stack and the contacts.

38. (New) An in-process substrate structure including a plurality of contact regions and a plurality of non-contact regions adjacent the contact regions on an upper surface of the substrate, the in-process substrate structure comprising:

a contact formed on each contact region, each contact having a top surface and two sidewall surfaces disposed between the top surface and the upper surface of the substrate, the top surface being heated to increase a vertical growth rate of the contact relative to a horizontal growth rate of the contact so that each sidewall remains substantially vertical and overlap of the contact into adjacent non contact regions due to lateral growth is limited.

39. (New) ~~1B~~ The substrate of claim 38 wherein the top surface is substantially parallel to the upper surface of the substrate.

40. (New) ~~1B~~ The substrate of claim 38 wherein the top surface is substantially horizontal.

41. (New) ~~1B~~ The substrate of claim 38 wherein the contact is heated by illuminating an upper surface of the contact with electromagnetic radiation.

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~~) The substrate
) The substrate
) The substrate
) perpendicular to the~~

cm
rashed

Country	Year	Population (millions)	Urban population (millions)	Urban population (%)
Algeria	1980	11.0	4.0	36.4
Algeria	1985	11.5	4.5	39.1
Algeria	1990	12.0	5.0	41.7
Algeria	1995	12.5	5.5	43.9
Algeria	2000	13.0	6.0	46.2
Algeria	2005	13.5	6.5	48.1
Algeria	2010	14.0	7.0	50.0
Algeria	2015	14.5	7.5	51.7
Algeria	2020	15.0	8.0	53.3
Algeria	2025	15.5	8.5	54.8
Algeria	2030	16.0	9.0	56.3
Algeria	2035	16.5	9.5	57.6
Algeria	2040	17.0	10.0	58.8
Algeria	2045	17.5	10.5	60.0
Algeria	2050	18.0	11.0	61.1
Algeria	2055	18.5	11.5	62.2
Algeria	2060	19.0	12.0	63.2
Algeria	2065	19.5	12.5	64.1
Algeria	2070	20.0	13.0	65.0
Algeria	2075	20.5	13.5	65.8
Algeria	2080	21.0	14.0	66.7
Algeria	2085	21.5	14.5	67.4
Algeria	2090	22.0	15.0	68.2
Algeria	2095	22.5	15.5	68.9
Algeria	2100	23.0	16.0	69.6
Algeria	2105	23.5	16.5	70.2
Algeria	2110	24.0	17.0	70.8
Algeria	2115	24.5	17.5	71.4
Algeria	2120	25.0	18.0	72.0
Algeria	2125	25.5	18.5	72.5
Algeria	2130	26.0	19.0	73.1
Algeria	2135	26.5	19.5	73.6
Algeria	2140	27.0	20.0	74.1
Algeria	2145	27.5	20.5	74.5
Algeria	2150	28.0	21.0	75.0
Algeria	2155	28.5	21.5	75.4
Algeria	2160	29.0	22.0	75.9
Algeria	2165	29.5	22.5	76.3
Algeria	2170	30.0	23.0	76.7
Algeria	2175	30.5	23.5	77.0
Algeria	2180	31.0	24.0	77.4
Algeria	2185	31.5	24.5	77.8
Algeria	2190	32.0	25.0	78.1
Algeria	2195	32.5	25.5	78.5
Algeria	2200	33.0	26.0	78.8
Algeria	2205	33.5	26.5	79.1
Algeria	2210	34.0	27.0	79.4
Algeria	2215	34.5	27.5	79.7
Algeria	2220	35.0	28.0	80.0
Algeria	2225	35.5	28.5	80.3
Algeria	2230	36.0	29.0	80.6
Algeria	2235	36.5	29.5	80.9
Algeria	2240	37.0	30.0	81.1
Algeria	2245	37.5	30.5	81.4
Algeria	2250	38.0	31.0	81.6
Algeria	2255	38.5	31.5	81.8
Algeria	2260	39.0	32.0	82.1
Algeria	2265	39.5	32.5	82.3
Algeria	2270	40.0	33.0	82.5
Algeria	2275	40.5	33.5	82.7
Algeria	2280	41.0	34.0	83.0
Algeria	2285	41.5	34.5	83.1
Algeria	2290	42.0	35.0	83.3
Algeria	2295	42.5	35.5	83.5
Algeria	2300	43.0	36.0	83.7
Algeria	2305	43.5	36.5	83.9
Algeria	2310	44.0	37.0	84.1
Algeria	2315	44.5	37.5	84.3
Algeria	2320	45.0	38.0	84.4
Algeria	2325	45.5	38.5	84.6
Algeria	2330	46.0	39.0	84.8
Algeria	2335	46.5	39.5	84.9
Algeria</				

51. (New) The substrate of claim 38 wherein the contact comprises silicon germanium. --